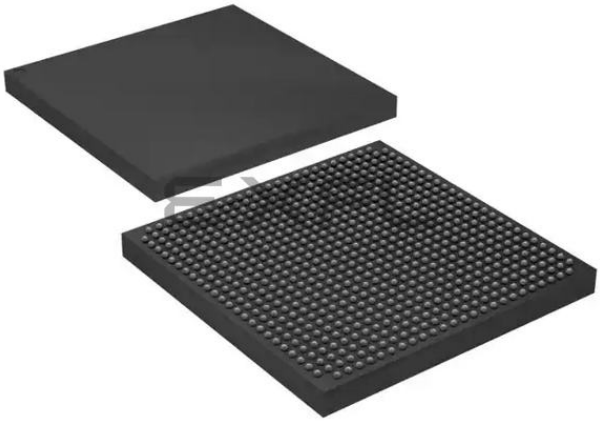

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	1664
Number of Logic Elements/Cells	16640
Total RAM Bits	212992
Number of I/O	502
Number of Gates	1052000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k400fc672-3

- Flexible clock management circuitry with up to four phase-locked loops (PLLs)
  - Built-in low-skew clock tree
  - Up to eight global clock signals
  - ClockLock® feature reducing clock delay and skew
  - ClockBoost® feature providing clock multiplication and division
  - ClockShift™ programmable clock phase and delay shifting
- Powerful I/O features
  - Compliant with peripheral component interconnect Special Interest Group (PCI SIG) ***PCI Local Bus Specification, Revision 2.2*** for 3.3-V operation at 33 or 66 MHz and 32 or 64 bits
  - Support for high-speed external memories, including DDR SDRAM and ZBT SRAM (ZBT is a trademark of Integrated Device Technology, Inc.)
  - Bidirectional I/O performance (t_{CO} + t_{SU}) up to 250 MHz
  - LVDS performance up to 840 Mbits per channel
  - Direct connection from I/O pins to local interconnect providing fast t_{CO} and t_{SU} times for complex logic
  - MultiVolt I/O interface support to interface with 1.8-V, 2.5-V, 3.3-V, and 5.0-V devices (see Table 3)
  - Programmable clamp to V_{CCIO}
  - Individual tri-state output enable control for each pin
  - Programmable output slew-rate control to reduce switching noise
  - Support for advanced I/O standards, including low-voltage differential signaling (LVDS), LVPECL, PCI-X, AGP, CTT, stub-series terminated logic (SSTL-3 and SSTL-2), Gunning transceiver logic plus (GTL+), and high-speed terminated logic (HSTL Class I)
  - Pull-up on I/O pins before and during configuration
- Advanced interconnect structure
  - Four-level hierarchical FastTrack® Interconnect structure providing fast, predictable interconnect delays
  - Dedicated carry chain that implements arithmetic functions such as fast adders, counters, and comparators (automatically used by software tools and megafunctions)
  - Dedicated cascade chain that implements high-speed, high-fan-in logic functions (automatically used by software tools and megafunctions)
  - Interleaved local interconnect allows one LE to drive 29 other LEs through the fast local interconnect
- Advanced packaging options
  - Available in a variety of packages with 144 to 1,020 pins (see Tables 4 through 7)
  - FineLine BGA® packages maximize board space efficiency
- Advanced software support
  - Software design support and automatic place-and-route provided by the Altera® Quartus® II development system for

The counter mode uses two three-input LUTs: one generates the counter data, and the other generates the fast carry bit. A 2-to-1 multiplexer provides synchronous loading, and another AND gate provides synchronous clearing. If the cascade function is used by an LE in counter mode, the synchronous clear or load overrides any signal carried on the cascade chain. The synchronous clear overrides the synchronous load. LEs in arithmetic mode can drive out registered and unregistered versions of the LUT output.

Clear & Preset Logic Control

Logic for the register's clear and preset signals is controlled by LAB-wide signals. The LE directly supports an asynchronous clear function. The Quartus II software Compiler can use a NOT-gate push-back technique to emulate an asynchronous preset. Moreover, the Quartus II software Compiler can use a programmable NOT-gate push-back technique to emulate simultaneous preset and clear or asynchronous load. However, this technique uses three additional LEs per register. All emulation is performed automatically when the design is compiled. Registers that emulate simultaneous preset and load will enter an unknown state upon power-up or when the chip-wide reset is asserted.

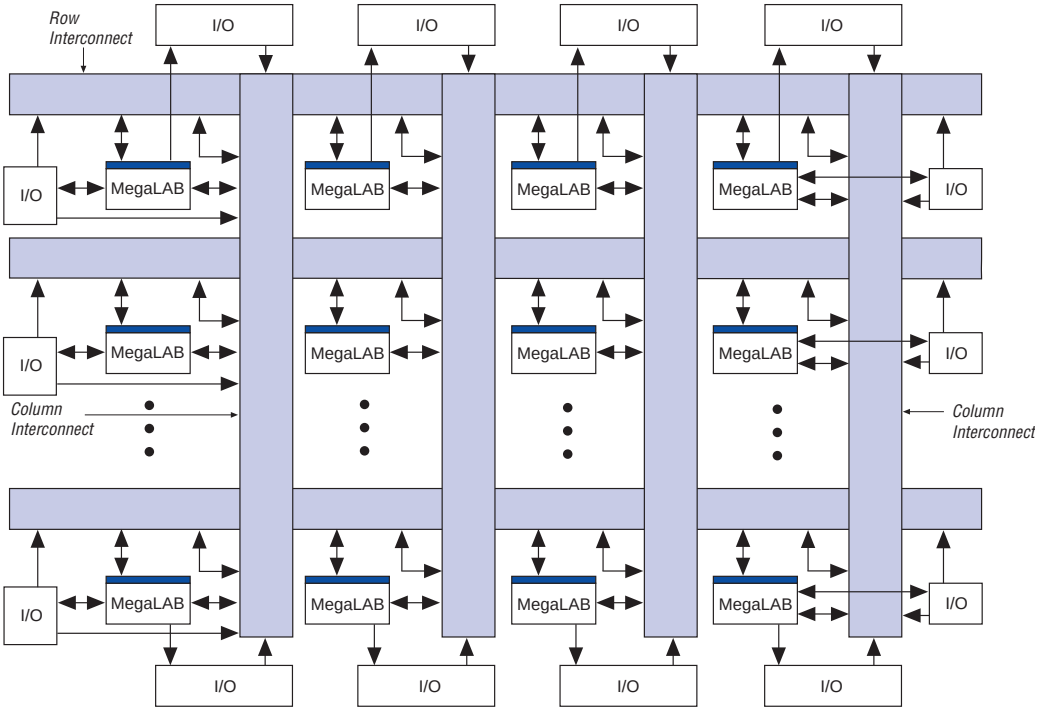
In addition to the two clear and preset modes, APEX 20K devices provide a chip-wide reset pin (DEV_CLRn) that resets all registers in the device. Use of this pin is controlled through an option in the Quartus II software that is set before compilation. The chip-wide reset overrides all other control signals. Registers using an asynchronous preset are preset when the chip-wide reset is asserted; this effect results from the inversion technique used to implement the asynchronous preset.

FastTrack Interconnect

In the APEX 20K architecture, connections between LEs, ESBs, and I/O pins are provided by the FastTrack Interconnect. The FastTrack Interconnect is a series of continuous horizontal and vertical routing channels that traverse the device. This global routing structure provides predictable performance, even in complex designs. In contrast, the segmented routing in FPGAs requires switch matrices to connect a variable number of routing paths, increasing the delays between logic resources and reducing performance.

The FastTrack Interconnect consists of row and column interconnect channels that span the entire device. The row interconnect routes signals throughout a row of MegaLAB structures; the column interconnect routes signals throughout a column of MegaLAB structures. When using the row and column interconnect, an LE, IOE, or ESB can drive any other LE, IOE, or ESB in a device. See Figure 9.

Figure 9. APEX 20K Interconnect Structure



A row line can be driven directly by LEs, IOEs, or ESBs in that row. Further, a column line can drive a row line, allowing an LE, IOE, or ESB to drive elements in a different row via the column and row interconnect. The row interconnect drives the MegaLAB interconnect to drive LEs, IOEs, or ESBs in a particular MegaLAB structure.

A column line can be directly driven by LEs, IOEs, or ESBs in that column. A column line on a device's left or right edge can also be driven by row IOEs. The column line is used to route signals from one row to another. A column line can drive a row line; it can also drive the MegaLAB interconnect directly, allowing faster connections between rows.

Figure 10 shows how the FastTrack Interconnect uses the local interconnect to drive LEs within MegaLAB structures.

Table 9. APEX 20K Routing Scheme

Source	Destination								
	Row I/O Pin	Column I/O Pin	LE	ESB	Local Interconnect	MegaLAB Interconnect	Row FastTrack Interconnect	Column FastTrack Interconnect	FastRow Interconnect
Row I/O Pin					✓	✓	✓	✓	
Column I/O Pin								✓	✓ (1)
LE					✓	✓	✓	✓	
ESB					✓	✓	✓	✓	
Local Interconnect	✓	✓	✓	✓					
MegaLAB Interconnect					✓				
Row FastTrack Interconnect						✓		✓	
Column FastTrack Interconnect						✓	✓		
FastRow Interconnect					✓ (1)				

Note to Table 9:
(1) This connection is supported in APEX 20KE devices only.

Product-Term Logic

The product-term portion of the MultiCore architecture is implemented with the ESB. The ESB can be configured to act as a block of macrocells on an ESB-by-ESB basis. Each ESB is fed by 32 inputs from the adjacent local interconnect; therefore, it can be driven by the MegaLAB interconnect or the adjacent LAB. Also, nine ESB macrocells feed back into the ESB through the local interconnect for higher performance. Dedicated clock pins, global signals, and additional inputs from the local interconnect drive the ESB control signals.

In product-term mode, each ESB contains 16 macrocells. Each macrocell consists of two product terms and a programmable register. Figure 13 shows the ESB in product-term mode.

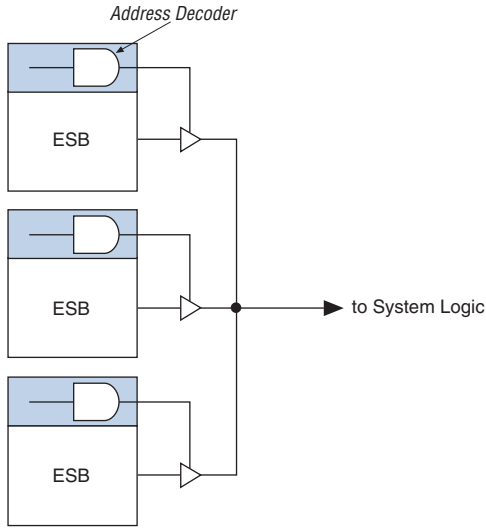
ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the MegaLAB or FastTrack Interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the MegaLAB and FastTrack Interconnect. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

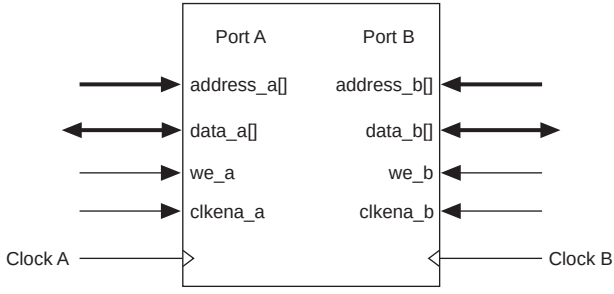
To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack Interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

Figure 18. Deep Memory Block Implemented with Multiple ESBs



The ESB implements two forms of dual-port memory: read/write clock mode and input/output clock mode. The ESB can also be used for bidirectional, dual-port memory applications in which two ports read or write simultaneously. To implement this type of dual-port memory, two or four ESBs are used to support two simultaneous reads or writes. This functionality is shown in Figure 19.

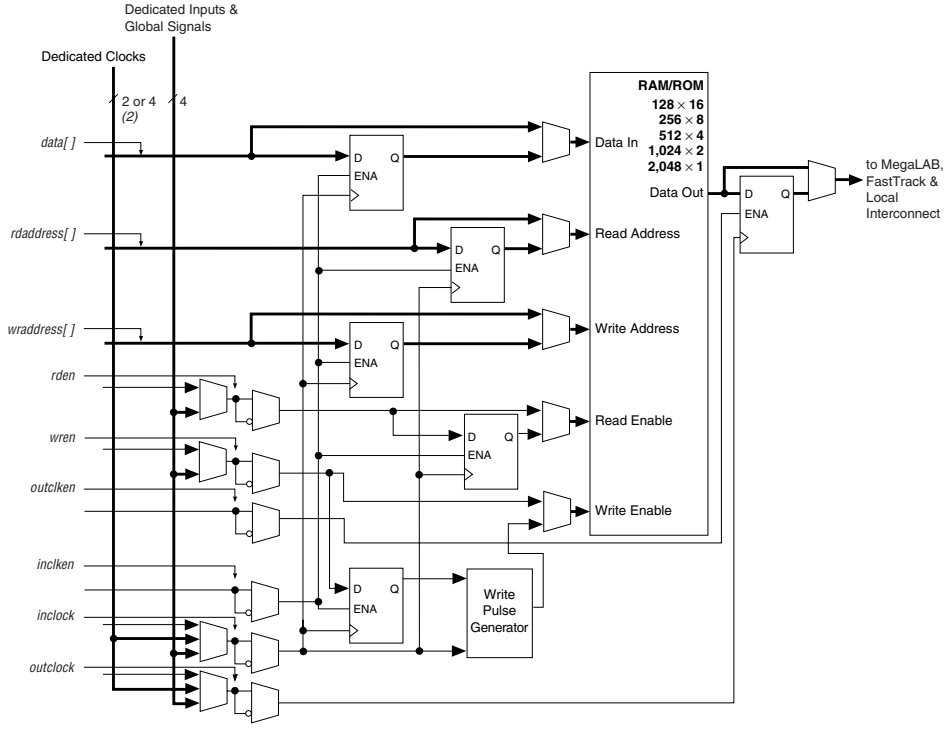
Figure 19. APEX 20K ESB Implementing Dual-Port RAM



Input/Output Clock Mode

The input/output clock mode contains two clocks. One clock controls all registers for inputs into the ESB: data input, WE, RE, read address, and write address. The other clock controls the ESB data output registers. The ESB also supports clock enable and asynchronous clear signals; these signals also control the reading and writing of registers independently. Input/output clock mode is commonly used for applications where the reads and writes occur at the same system frequency, but require different clock enable signals for the input and output registers. Figure 21 shows the ESB in input/output clock mode.

Figure 21. ESB in Input/Output Clock Mode *Note (1)*

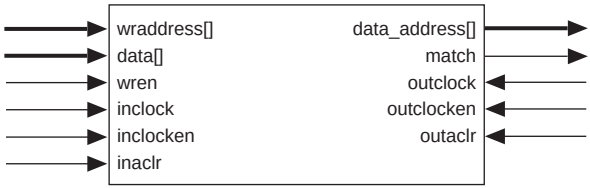


Notes to Figure 21:
(1) All registers can be cleared asynchronously by ESB local interconnect signals, global signals, or the chip-wide reset.
(2) APEX 20KE devices have four dedicated clocks.

Single-Port Mode

The APEX 20K ESB also supports a single-port mode, which is used when simultaneous reads and writes are not required. See Figure 22.

Figure 23. APEX 20KE CAM Block Diagram



CAM can be used in any application requiring high-speed searches, such as networking, communications, data compression, and cache management.

The APEX 20KE on-chip CAM provides faster system performance than traditional discrete CAM. Integrating CAM and logic into the APEX 20KE device eliminates off-chip and on-chip delays, improving system performance.

When in CAM mode, the ESB implements 32-word, 32-bit CAM. Wider or deeper CAM can be implemented by combining multiple CAMs with some ancillary logic implemented in LEs. The Quartus II software combines ESBs and LEs automatically to create larger CAMs.

CAM supports writing "don't care" bits into words of the memory. The "don't-care" bit can be used as a mask for CAM comparisons; any bit set to "don't-care" has no effect on matches.

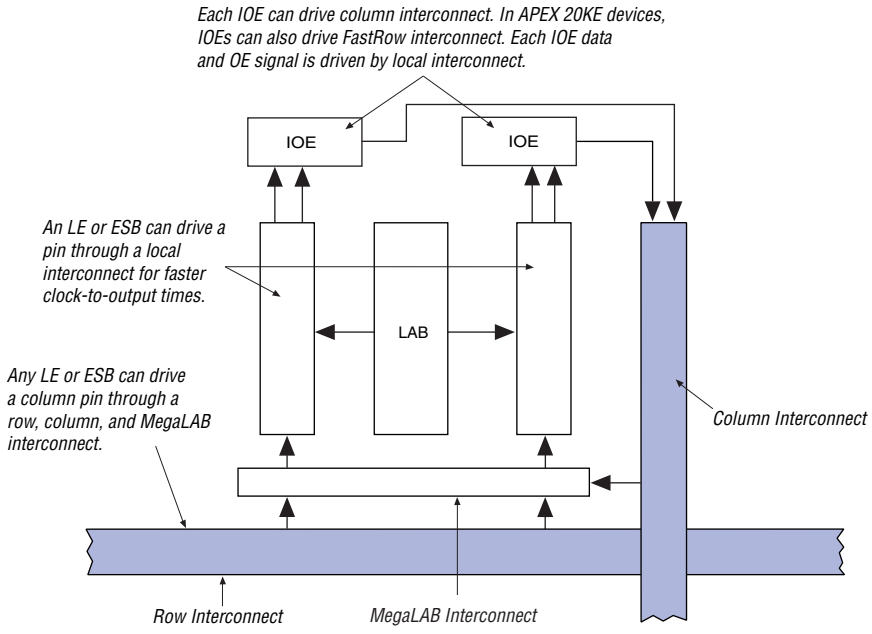
The output of the CAM can be encoded or unencoded. When encoded, the ESB outputs an encoded address of the data's location. For instance, if the data is located in address `12`, the ESB output is `12`. When unencoded, the ESB uses its 16 outputs to show the location of the data over two clock cycles. In this case, if the data is located in address `12`, the 12th output line goes high. When using unencoded outputs, two clock cycles are required to read the output because a 16-bit output bus is used to show the status of 32 words.

The encoded output is better suited for designs that ensure duplicate data is not written into the CAM. If duplicate data is written into two locations, the CAM's output will be incorrect. If the CAM may contain duplicate data, the unencoded output is a better solution; CAM with unencoded outputs can distinguish multiple data locations.

CAM can be pre-loaded with data during configuration, or it can be written during system operation. In most cases, two clock cycles are required to write each word into CAM. When "don't-care" bits are used, a third clock cycle is required.

Figure 28 shows how a column IOE connects to the interconnect.

Figure 28. Column IOE Connection to the Interconnect



Dedicated Fast I/O Pins

APEX 20KE devices incorporate an enhancement to support bidirectional pins with high internal fanout such as PCI control signals. These pins are called Dedicated Fast I/O pins (`FAST1`, `FAST2`, `FAST3`, and `FAST4`) and replace dedicated inputs. These pins can be used for fast clock, clear, or high fanout logic signal distribution. They also can drive out. The Dedicated Fast I/O pin data output and tri-state control are driven by local interconnect from the adjacent MegaLAB for high speed.

Advanced I/O Standard Support

APEX 20KE IOEs support the following I/O standards: LVTTL, LVCMOS, 1.8-V I/O, 2.5-V I/O, 3.3-V PCI, PCI-X, 3.3-V AGP, LVDS, LVPECL, GTL+, CTT, HSTL Class I, SSTL-3 Class I and II, and SSTL-2 Class I and II.

For more information on I/O standards supported by APEX 20KE devices, see *Application Note 117 (Using Selectable I/O Standards in Altera Devices)*.

The APEX 20KE device contains eight I/O banks. In QFP packages, the banks are linked to form four I/O banks. The I/O banks directly support all standards except LVDS and LVPECL. All I/O banks can support LVDS and LVPECL with the addition of external resistors. In addition, one block within a bank contains circuitry to support high-speed True-LVDS and LVPECL inputs, and another block within a particular bank supports high-speed True-LVDS and LVPECL outputs. The LVDS blocks support all of the I/O standards. Each I/O bank has its own VCCIO pins. A single device can support 1.8-V, 2.5-V, and 3.3-V interfaces; each bank can support a different standard independently. Each bank can also use a separate V_{REF} level so that each bank can support any of the terminated standards (such as SSTL-3) independently. Within a bank, any one of the terminated standards can be supported. EP20K300E and larger APEX 20KE devices support the LVDS interface for data pins (smaller devices support LVDS clock pins, but not data pins). All EP20K300E and larger devices support the LVDS interface for data pins up to 155 Mbit per channel; EP20K400E devices and larger with an X-suffix on the ordering code add a serializer/deserializer circuit and PLL for higher-speed support.

Each bank can support multiple standards with the same VCCIO for output pins. Each bank can support one voltage-referenced I/O standard, but it can support multiple I/O standards with the same VCCIO voltage level. For example, when VCCIO is 3.3 V, a bank can support LVTTL, LVCMOS, 3.3-V PCI, and SSTL-3 for inputs and outputs.

When the LVDS banks are not used as LVDS I/O banks, they support all of the other I/O standards. Figure 29 shows the arrangement of the APEX 20KE I/O banks.

Table 18. APEX 20KE Clock Input & Output Parameters (Part 2 of 2) Note (1)

Symbol	Parameter	I/O Standard	-1X Speed Grade		-2X Speed Grade		Units
			Min	Max	Min	Max	
f_{IN}	Input clock frequency	3.3-V LVTTL	1.5	290	1.5	257	MHz
		2.5-V LVTTL	1.5	281	1.5	250	MHz
		1.8-V LVTTL	1.5	272	1.5	243	MHz
		GTL+	1.5	303	1.5	261	MHz
		SSTL-2 Class I	1.5	291	1.5	253	MHz
		SSTL-2 Class II	1.5	291	1.5	253	MHz
		SSTL-3 Class I	1.5	300	1.5	260	MHz
		SSTL-3 Class II	1.5	300	1.5	260	MHz
		LVDS	1.5	420	1.5	350	MHz

Notes to Tables 17 and 18:

(1) All input clock specifications must be met. The PLL may not lock onto an incoming clock if the clock specifications are not met, creating an erroneous clock within the device.
(2) The maximum lock time is 40 µs or 2000 input clock cycles, whichever occurs first.
(3) Before configuration, the PLL circuits are disable and powered down. During configuration, the PLLs are still disabled. The PLLs begin to lock once the device is in the user mode. If the clock enable feature is used, lock begins once the `CLKLK_ENA` pin goes high in user mode.
(4) The PLL VCO operating range is 200 MHz ð f_{VCO} ð 840 MHz for LVDS mode.

SignalTap Embedded Logic Analyzer

APEX 20K devices include device enhancements to support the SignalTap embedded logic analyzer. By including this circuitry, the APEX 20K device provides the ability to monitor design operation over a period of time through the IEEE Std. 1149.1 (JTAG) circuitry; a designer can analyze internal logic at speed without bringing internal signals to the I/O pins. This feature is particularly important for advanced packages such as FineLine BGA packages because adding a connection to a pin during the debugging process can be difficult after a board is designed and manufactured.

Table 29. APEX 20KE Device DC Operating Conditions *Notes (7), (8), (9)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level LVTTL, CMOS, or 3.3-V PCI input voltage		1.7, 0.5 × V_{CCIO} *(10)*		4.1	V
V_{IL}	Low-level LVTTL, CMOS, or 3.3-V PCI input voltage		–0.5		0.8, 0.3 × V_{CCIO} *(10)*	V
V_{OH}	3.3-V high-level LVTTL output voltage	I_{OH} = –12 mA DC, V_{CCIO} = 3.00 V *(11)*	2.4			V
	3.3-V high-level LVCMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(11)*	V_{CCIO} – 0.2			V
	3.3-V high-level PCI output voltage	I_{OH} = –0.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(11)*	0.9 × V_{CCIO}			V
	2.5-V high-level output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 2.30 V *(11)*	2.1			V
		I_{OH} = –1 mA DC, V_{CCIO} = 2.30 V *(11)*	2.0			V
		I_{OH} = –2 mA DC, V_{CCIO} = 2.30 V *(11)*	1.7			V
V_{OL}	3.3-V low-level LVTTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(12)*			0.4	V
	3.3-V low-level LVCMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(12)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(12)*			0.1 × V_{CCIO}	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.30 V *(12)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.30 V *(12)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.30 V *(12)*			0.7	V
I_I	Input pin leakage current	V_I = 4.1 to –0.5 V *(13)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 4.1 to –0.5 V *(13)*	–10		10	µA
I_{CC0}	V_{CC} supply current (standby) (All ESBs in power-down mode)	V_I = ground, no load, no toggling inputs, -1 speed grade		10		mA
		V_I = ground, no load, no toggling inputs, -2, -3 speed grades		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(14)*	20		50	kΩ
		V_{CCIO} = 2.375 V *(14)*	30		80	kΩ
		V_{CCIO} = 1.71 V *(14)*	60		150	kΩ

Figure 37. APEX 20KE f_{MAX} Timing Model

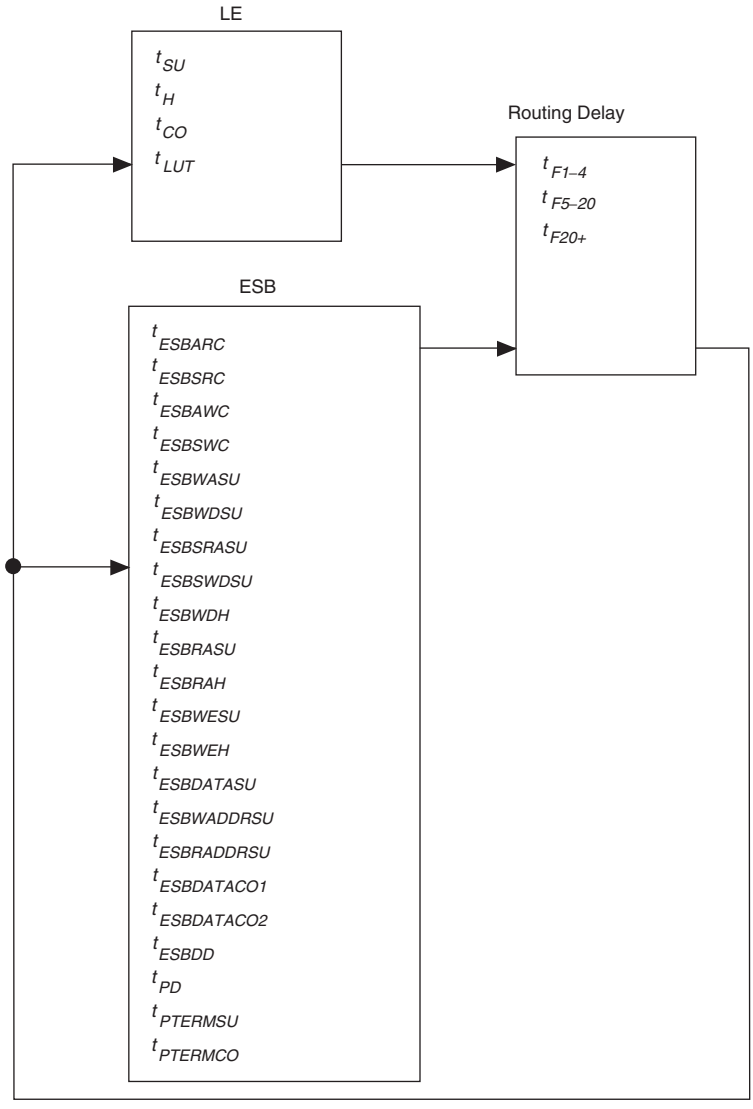


Table 31. APEX 20K f_{MAX} Timing Parameters (Part 2 of 2)	
Symbol	**Parameter**
$t_{ESBDATACO2}$	ESB clock-to-output delay without output registers
t_{ESBDD}	ESB data-in to data-out delay for RAM mode
t_{PD}	ESB macrocell input to non-registered output
$t_{PTERMSU}$	ESB macrocell register setup time before clock
$t_{PTERMCO}$	ESB macrocell register clock-to-output delay
t_{F1-4}	Fanout delay using local interconnect
t_{F5-20}	Fanout delay using MegaLab Interconnect
t_{F20+}	Fanout delay using FastTrack Interconnect
t_{CH}	Minimum clock high time from clock pin
t_{CL}	Minimum clock low time from clock pin
t_{CLRP}	LE clear pulse width
t_{PREP}	LE preset pulse width
t_{ESBCH}	Clock high time
t_{ESBCL}	Clock low time
t_{ESBWP}	Write pulse width
t_{ESBRP}	Read pulse width

Tables 32 and 33 describe APEX 20K external timing parameters.

Table 32. APEX 20K External Timing Parameters *Note (1)*	
Symbol	**Clock Parameter**
t_{INSU}	Setup time with global clock at IOE register
t_{INH}	Hold time with global clock at IOE register
t_{OUTCO}	Clock-to-output delay with global clock at IOE register

Table 33. APEX 20K External Bidirectional Timing Parameters *Note (1)*		
Symbol	**Parameter**	**Conditions**
$t_{INSUBIDIR}$	Setup time for bidirectional pins with global clock at same-row or same-column LE register	
$t_{INHBIDIR}$	Hold time for bidirectional pins with global clock at same-row or same-column LE register	
$t_{OUTCOBIDIR}$	Clock-to-output delay for bidirectional pins with global clock at IOE register	C1 = 10 pF
$t_{XZBIDIR}$	Synchronous IOE output buffer disable delay	C1 = 10 pF
$t_{ZXBIDIR}$	Synchronous IOE output buffer enable delay, slow slew rate = off	C1 = 10 pF

Note to Tables 32 and 33:
(1) These timing parameters are sample-tested only.

Tables 34 through 37 show APEX 20KE LE, ESB, routing, and functional timing microparameters for the f_{MAX} timing model.

Table 34. APEX 20KE LE Timing Microparameters

Symbol	Parameter
t_{SU}	LE register setup time before clock
t_{H}	LE register hold time after clock
t_{CO}	LE register clock-to-output delay
t_{LUT}	LUT delay for data-in to data-out

Table 35. APEX 20KE ESB Timing Microparameters

Symbol	Parameter
t_{ESBARC}	ESB Asynchronous read cycle time
t_{ESBSRC}	ESB Synchronous read cycle time
t_{ESBAWC}	ESB Asynchronous write cycle time
t_{ESBSWC}	ESB Synchronous write cycle time
$t_{ESBWASU}$	ESB write address setup time with respect to WE
t_{ESBWAH}	ESB write address hold time with respect to WE
$t_{ESBWDSU}$	ESB data setup time with respect to WE
t_{ESBWDH}	ESB data hold time with respect to WE
$t_{ESBRASU}$	ESB read address setup time with respect to RE
t_{ESBRAH}	ESB read address hold time with respect to RE
$t_{ESBWESU}$	ESB WE setup time before clock when using input register
t_{ESBWEH}	ESB WE hold time after clock when using input register
$t_{ESBDATASU}$	ESB data setup time before clock when using input register
$t_{ESBDATAH}$	ESB data hold time after clock when using input register
$t_{ESBWADDRSU}$	ESB write address setup time before clock when using input registers
$t_{ESBRADDRSU}$	ESB read address setup time before clock when using input registers
$t_{ESBDATACO1}$	ESB clock-to-output delay when using output registers
$t_{ESBDATACO2}$	ESB clock-to-output delay without output registers
t_{ESBDD}	ESB data-in to data-out delay for RAM mode
t_{PD}	ESB Macrocell input to non-registered output
$t_{PTERMSU}$	ESB Macrocell register setup time before clock
$t_{PTERMCO}$	ESB Macrocell register clock-to-output delay

Table 41. EP20K200 f_{MAX} Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Units
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.5		0.6		0.8		ns
t_{H}	0.7		0.8		1.0		ns
t_{CO}		0.3		0.4		0.5	ns
t_{LUT}		0.8		1.0		1.3	ns
t_{ESBRC}		1.7		2.1		2.4	ns
t_{ESBWC}		5.7		6.9		8.1	ns
$t_{ESBWESU}$	3.3		3.9		4.6		ns
$t_{ESBDATASU}$	2.2		2.7		3.1		ns
$t_{ESBDATAH}$	0.6		0.8		0.9		ns
$t_{ESBADDRSU}$	2.4		2.9		3.3		ns
$t_{ESBDATACO1}$		1.3		1.6		1.8	ns
$t_{ESBDATACO2}$		2.6		3.1		3.6	ns
t_{ESBDD}		2.5		3.3		3.6	ns
t_{PD}		2.5		3.0		3.6	ns
$t_{PTERMSU}$	2.3		2.7		3.2		ns
$t_{PTERMCO}$		1.5		1.8		2.1	ns
t_{F1-4}		0.5		0.6		0.7	ns
t_{F5-20}		1.6		1.7		1.8	ns
t_{F20+}		2.2		2.2		2.3	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns
t_{CLRP}	0.3		0.4		0.4		ns
t_{PREP}	0.4		0.5		0.5		ns
t_{ESBCH}	2.0		2.5		3.0		ns
t_{ESBCL}	2.0		2.5		3.0		ns
t_{ESBWP}	1.6		1.9		2.2		ns
t_{ESBRP}	1.0		1.3		1.4		ns

Table 42. EP20K400 f_{MAX} Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Units
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.1		0.3		0.6		ns
t_{H}	0.5		0.8		0.9		ns
t_{CO}		0.1		0.4		0.6	ns
t_{LUT}		1.0		1.2		1.4	ns
t_{ESBRC}		1.7		2.1		2.4	ns
t_{ESBWC}		5.7		6.9		8.1	ns
$t_{ESBWESU}$	3.3		3.9		4.6		ns
$t_{ESBDATASU}$	2.2		2.7		3.1		ns
$t_{ESBDATAH}$	0.6		0.8		0.9		ns
$t_{ESBADDRSU}$	2.4		2.9		3.3		ns
$t_{ESBDATACO1}$		1.3		1.6		1.8	ns
$t_{ESBDATACO2}$		2.5		3.1		3.6	ns
t_{ESBDD}		2.5		3.3		3.6	ns
t_{PD}		2.5		3.1		3.6	ns
$t_{PTERMSU}$	1.7		2.1		2.4		ns
$t_{PTERMCO}$		1.0		1.2		1.4	ns
t_{F1-4}		0.4		0.5		0.6	ns
t_{F5-20}		2.6		2.8		2.9	ns
t_{F20+}		3.7		3.8		3.9	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns
t_{CLRP}	0.5		0.6		0.8		ns
t_{PREP}	0.5		0.5		0.5		ns
t_{ESBCH}	2.0		2.5		3.0		ns
t_{ESBCL}	2.0		2.5		3.0		ns
t_{ESBWP}	1.5		1.9		2.2		ns
t_{ESBRP}	1.0		1.2		1.4		ns

Tables 43 through 48 show the I/O external and external bidirectional timing parameter values for EP20K100, EP20K200, and EP20K400 APEX 20K devices.

Table 68. EP20K160E f_{MAX} ESB Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.65		2.02		2.11	ns
t_{ESBSRC}		2.21		2.70		3.11	ns
t_{ESBAWC}		3.04		3.79		4.42	ns
t_{ESBSWC}		2.81		3.56		4.10	ns
$t_{ESBWASU}$	0.54		0.66		0.73		ns
t_{ESBWAH}	0.36		0.45		0.47		ns
$t_{ESBWDSU}$	0.68		0.81		0.94		ns
t_{ESBWDH}	0.36		0.45		0.47		ns
$t_{ESBRASU}$	1.58		1.87		2.06		ns
t_{ESBRAH}	0.00		0.00		0.01		ns
$t_{ESBWESU}$	1.41		1.71		2.00		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.02		-0.03		0.09		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.14		0.17		0.35		ns
$t_{ESBRADDRSU}$	0.21		0.27		0.43		ns
$t_{ESBDATACO1}$		1.04		1.30		1.46	ns
$t_{ESBDATACO2}$		2.15		2.70		3.16	ns
t_{ESBDD}		2.69		3.35		3.97	ns
t_{PD}		1.55		1.93		2.29	ns
$t_{PTERMSU}$	1.01		1.23		1.52		ns
$t_{PTERMCO}$		1.06		1.32		1.04	ns

Table 78. EP20K200E External Bidirectional Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.81		3.19		3.54		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	5.12	2.00	5.62	2.00	6.11	ns
$t_{XZBIDIR}$		7.51		8.32		8.67	ns
$t_{ZXBIDIR}$		7.51		8.32		8.67	ns
$t_{INSUBIDIRPLL}$	3.30		3.64		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	3.01	0.50	3.36	-	-	ns
$t_{XZBIDIRPLL}$		5.40		6.05		-	ns
$t_{ZXBIDIRPLL}$		5.40		6.05		-	ns

Tables 79 through 84 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K300E APEX 20KE devices.

Table 79. EP20K300E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.16		0.17		0.18		ns
t_{H}	0.31		0.33		0.38		ns
t_{CO}		0.28		0.38		0.51	ns
t_{LUT}		0.79		1.07		1.43	ns

Revision History

The information contained in the *APEX 20K Programmable Logic Device Family Data Sheet* version 5.1 supersedes information published in previous versions.

Version 5.1

APEX 20K Programmable Logic Device Family Data Sheet version 5.1 contains the following changes:

- In version 5.0, the VI input voltage spec was updated in Table 28 on page 63.
- In version 5.0, *Note (5)* to Tables 27 through 30 was revised.
- Added *Note (2)* to Figure 21 on page 33.

Version 5.0

APEX 20K Programmable Logic Device Family Data Sheet version 5.0 contains the following changes:

- Updated Tables 23 through 26. Removed 2.5-V operating condition tables because all APEX 20K devices are now 5.0-V tolerant.
- Updated conditions in Tables 33, 38 and 39.
- Updated data for $t_{ESBDATAH}$ parameter.

Version 4.3

APEX 20K Programmable Logic Device Family Data Sheet version 4.3 contains the following changes:

- Updated Figure 20.
- Updated *Note (2)* to Table 13.
- Updated notes to Tables 27 through 30.

Version 4.2

APEX 20K Programmable Logic Device Family Data Sheet version 4.2 contains the following changes:

- Updated Figure 29.
- Updated *Note (1)* to Figure 29.